

## Silicon nanopyramid texture fabricated by one-step solution process and its application to silicon heterojunction solar cells

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A novel method to fabricate crystalline silicon (c-Si) nanometer-sized pyramid (nanopyramid) texture with low etching margin using one-step solution process is reported. Recently, thin (<120  $\mu\text{m}$ ) c-Si solar cells have attracted much attention as a promising way to significantly cut down the production cost of the solar cell modules [1-3]. Compared to the conventional micron-sized Si pyramids, the nanopyramid texture is advantageous particularly for thin c-Si solar cells in minimizing the etching margin. At the same time, a smaller pyramid size allows to narrow the screen-printed Ag fingers, which in turn improves the  $J_{\text{sc}}$  of solar cells and reduces the Ag consumption [4]. Furthermore, Si nanopyramid texture is expected to be suited to perovskite/Si tandem cells [5], as it offers the potential of conformal deposition of perovskite top cell on top of the textured Si surface by means of low-cost solution-based deposition techniques.

In this contribution, we propose a new methodology of fabricating Si nanopyramid texture featuring both excellent anti-reflection performance and relatively low etching margin using an  $\text{AgNO}_3$ -assisted alkaline solution. After cleaning processes with acetone and deionized water, the planar Si wafer was textured by dipping in a mixed solution, which contains KOH: Pure EtchTK81(Hayashi Pure Chemicals Ltd., surfactant) and acid solution of HF:  $\text{AgNO}_3$ , for 15 min at 70°C. The texture size can be tuned by changing the concentration of HF:  $\text{AgNO}_3$  solution. Figures 1a and 1b show the top-view and cross-sectional SEM images, respectively, showing that Si nanopyramids with a height of 300-500 nm were successfully formed on the Si surface. The etching margin of this structure was 3.4  $\mu\text{m}$ . An even lower optical reflection is realized in comparison with the reference micron-sized pyramid texture (Fig. 2). Si heterojunction solar cells with Si nanopyramid textures were fabricated, demonstrating higher  $J_{\text{sc}}$  and efficiency compared with the cells with the conventional micron-sized Si pyramids.

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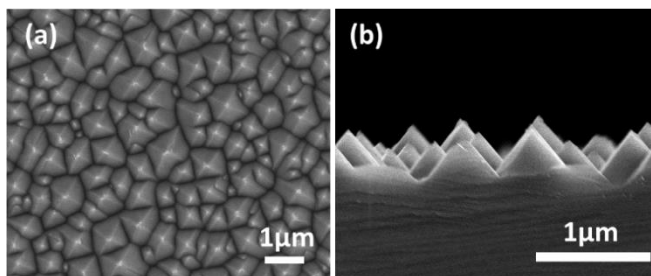


Fig. 1. Si nanopyramids etched by  $\text{AgNO}_3$ -assisted alkaline solution (a) top view and (b) cross-sectional view.

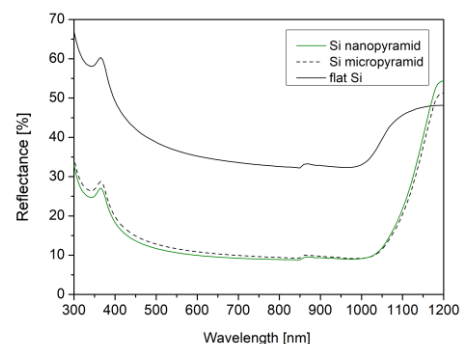


Fig. 2. Optical reflectance of the textured Si wafers with nano/micropyramids and flat Si wafer.

### References

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